

N-channel 25 V 0.99 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 4 July 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	25	V
I_D	drain current	T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	272	W
Tj	junction temperature			-55	-	175	°C
Static char	racteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$		-	0.95	1.25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_i = 25 ^{\circ}\text{C}; \text{ see Figure 12}$		-	0.75	0.99	mΩ



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic o	characteristics					
Q_{GD}	gate-drain charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	14	-	nC
Q _{G(tot)}	total gate charge	V_{GS} = 4.5 V; I_D = 25 A; V_{DS} = 12 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	51	-	nC

^[1] Continuous current is limited by package

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source	mb (D
3	S	source		$G \longrightarrow \overline{A}$
4	G	gate	[q]	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN0R9-25YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	25	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ		-	25	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	100	Α
		T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; see Figure 4		-	1563	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	272	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		920	-	V
Source-dra	nin diode					
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	1563	Α
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 25 V; unclamped; R_{GS} = 50 Ω; see Figure 3		-	342	mJ

[1] Continuous current is limited by package

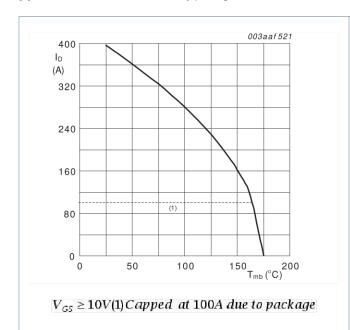


Fig 1. Continuous drain current as a function of mounting base temperature

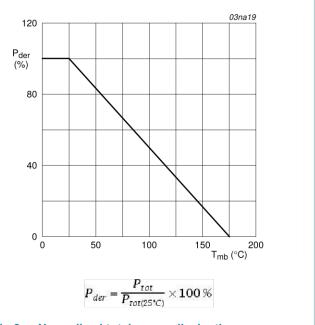
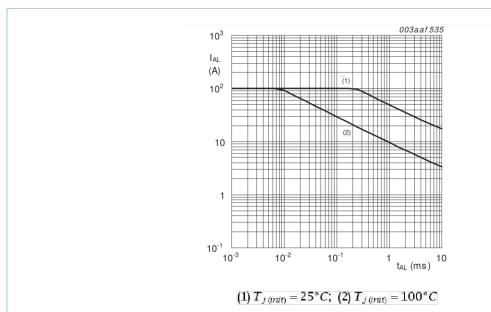


Fig 2. Normalized total power dissipation as a function of mounting base temperature

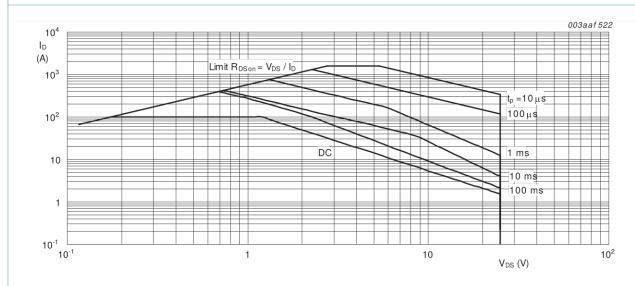
PSMN0R9-25YLC

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Single pulse avalanche rating; avalanche current as a function of avalanche time



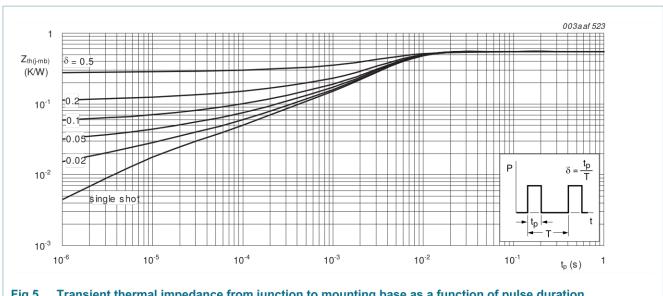
 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

Thermal characteristics

Thermal characteristics Table 5.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	0.45	0.55	K/W



Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source breakdown	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	25	-	-	V
	voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = -55 °C	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 10	1.05	1.41	1.95	V
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; see <u>Figure 11</u>	-	-	2.25	V
		I_D = 10 mA; V_{DS} = V_{GS} ; T_j = 150 °C	0.5	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		V_{DS} = 25 V; V_{GS} = 0 V; T_j = 150 °C	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nΑ
		V_{GS} = -16 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nΑ
R _{DSon} drain-source on-state resistance		V_{GS} = 4.5 V; I_{D} = 25 A; T_{j} = 25 °C; see <u>Figure 12</u>	-	0.95	1.25	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	2.125	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see Figure 12	-	0.75	0.99	mΩ
	V_{GS} = 10 V; I_D = 25 A; T_j = 150 °C; see Figure 12; see Figure 13	-	-	1.68	mΩ	
R_G	internal gate resistance (AC)	f = 1 MHz	-	1.1	2.2	Ω
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 12 V; V_{GS} = 10 V; see Figure 14; see Figure 15	-	110	-	nC
		I _D = 25 A; V _{DS} = 12 V; V _{GS} = 4.5 V; see <u>Figure 15</u> ; see <u>Figure 14</u>	-	51	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V; see Figure 14	-	104	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	14.8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	10.5	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	4.4	-	nC
Q_{GD}	gate-drain charge		-	14	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 25 A; V _{DS} = 12 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.4	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V; } V_{GS} = 0 \text{ V; } f = 1 \text{ MHz;}$	-	6775	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	1437	-	pF
C _{rss}	reverse transfer capacitance	-	-	573	-	pF

Table 6. Characteristics ...continued

	The state of the s					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	V_{DS} = 12 V; R_L = 0.5 Ω ; V_{GS} = 4.5 V;	-	42.5	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	74	-	ns
t _{d(off)}	turn-off delay time		-	103.5	-	ns
t _f	fall time		-	55	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	31.57	-	nC
Source-drai	n diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	8.0	1.1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	48	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}$	-	60	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_{S} \text{ 25 A;}$ $dI_{S}/dt = -100 \text{ A/}\mu\text{s; } V_{DS} = 12 \text{ V;}$ see Figure 18	-	26.3	-	ns
t_b	reverse recovery fall time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A;}$ $dI_S/dt = -100 \text{ A/}\mu\text{s; } V_{DS} = 12 \text{ V;}$ see Figure 18	-	21.7	-	ns

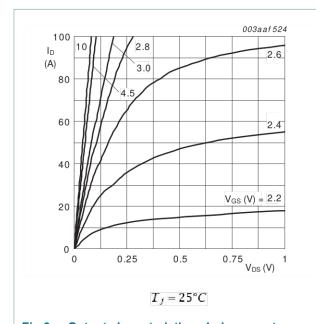


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

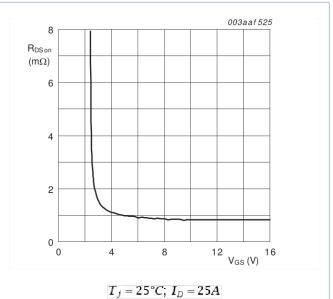


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

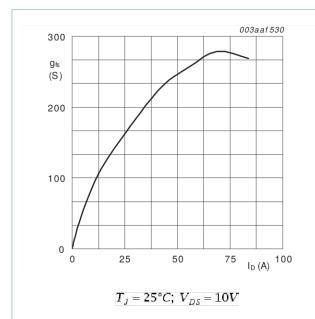


Fig 8. Forward transconductance as a function of drain current; typical values

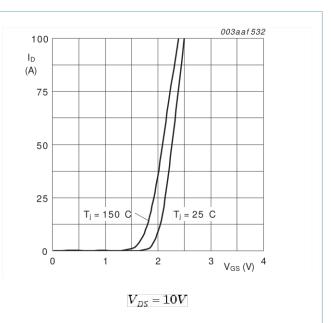
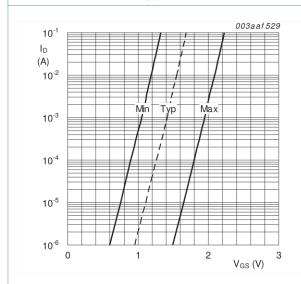


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values



 $T_j = 25^{\circ}C; \ V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

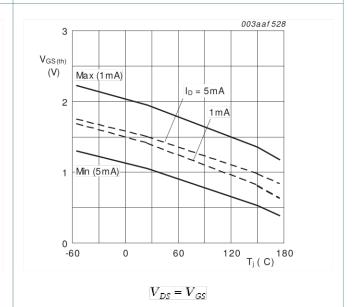


Fig 11. Gate-source threshold voltage as a function of junction temperature

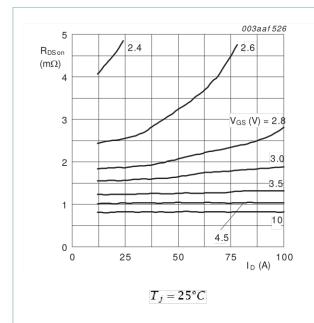


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

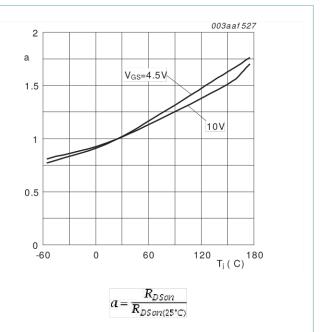


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

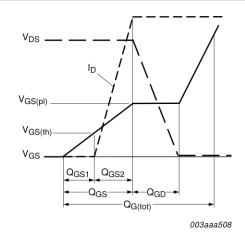


Fig 14. Gate charge waveform definitions

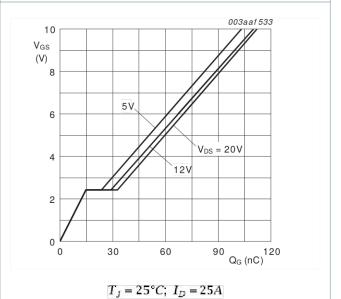


Fig 15. Gate-source voltage as a function of gate charge; typical values

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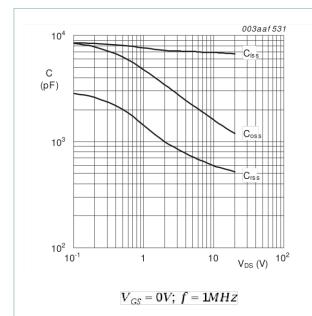


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

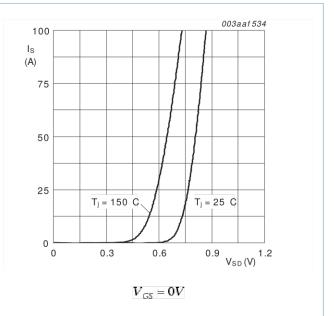


Fig 17. Source current as a function of source-drain voltage; typical values

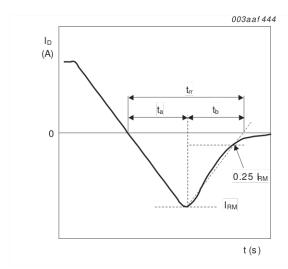


Fig 18. Reverse recovery timing definition

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7. Package outline

Plastic single-ended surface-mounted package (LFPAK; Power-SO8); 4 leads

SOT669

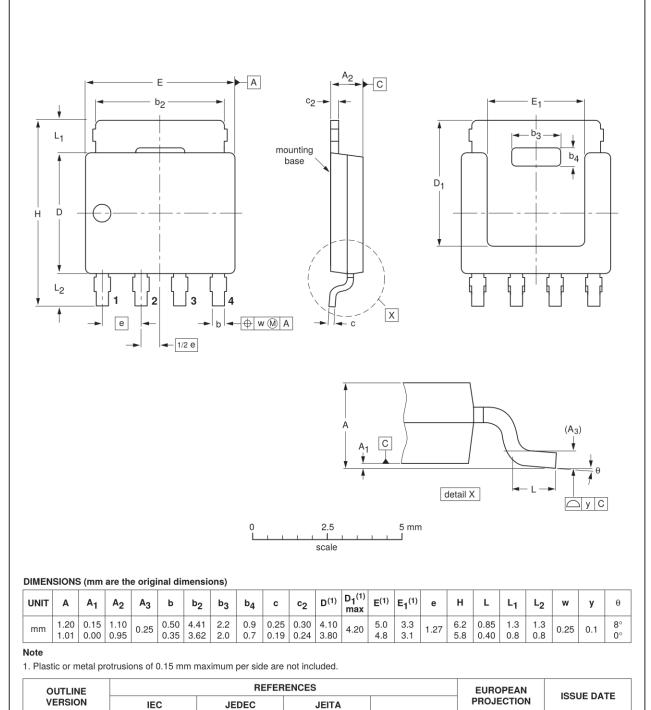


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

MO-235

PSMN0R9-25YLC

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06-03-16

11-03-25

SOT669

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PSMN0R9-25YLC v.2	20110704	Product data sheet	-	PSMN0R9-25YLC v.1	
Modifications: • Various changes to content.					
PSMN0R9-25YLC v.1	20101202	Product data sheet	-	-	

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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Product data sheet

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